

PSMN4R3-40MSH

N-channel 40 V, 4.3 m Ω , standard level MOSFET in LFPAK33 using NextPower-S3 technology

27 April 2020

Product data sheet

1. General description

95 A, standard level N-channel enhancement mode MOSFET in 175 °C LFPAK33 package using advanced TrenchMOS Superjunction technology. This product has been designed and qualified for high efficiency applications at high switching frequencies.

2. Features and benefits

- Avalanche rated, 100% tested
- NextPower-S3 technology delivers 'superfast switching with soft body-diode recovery'
- Low Q_{RR}, Q_G and Q_{GD} for high system efficiency, especially at high switching frequencies
- Low spiking and ringing for low EMI designs
- High reliability clip bonded and solder die attach Mini Power SO8 package; no glue, no wire bonds, qualified to 175 °C
- Exposed leads can be wave soldered, visual solder joint inspection and high quality solder joints
- · Low parasitic inductance and resistance

3. Applications

- · Secondary side synchronous rectification
- DC-to-DC converters
- Brushless DC motor drive
- LED lighting

4. Quick reference data

Table 1. Quick reference data

Symbol	Parameter	Conditions		Min	Тур	Max	Unit
V _{DS}	drain-source voltage	25 °C ≤ T _j ≤ 175 °C		-	-	40	V
I _D	drain current	V _{GS} = 10 V; T _{mb} = 25 °C; <u>Fig. 2</u>	[1]	-	-	95	Α
P _{tot}	total power dissipation	T _{mb} = 25 °C; <u>Fig. 1</u>		-	-	90	W
Tj	junction temperature			-55	-	175	°C
Static characte	eristics						
R _{DSon}	drain-source on-state resistance	$V_{GS} = 10 \text{ V}; I_D = 25 \text{ A}; T_j = 25 ^{\circ}\text{C};$ Fig. 10		-	3.5	4.3	mΩ
Dynamic characteristics							
Q_{GD}	gate-drain charge	I _D = 25 A; V _{DS} = 20 V; V _{GS} = 10 V;		1.1	3.6	7.3	nC
Q _{G(tot)}	total gate charge	Fig. 12; Fig. 13		15	23	32	nC

^{[1] 95}A Continuous current has been successfully demonstrated during application tests. Practically the current will be limited by PCB, thermal design and operating temperature.



5. Pinning information

Table 2. Pinning information

Pin	Symbol	Description	Simplified outline	Graphic symbol
1	S	source		D
2	S	source		
3	S	source		G—(F)
4	G	gate		mbb076 S
mb	D	Mounting base; connected to drain	1 2 3 4 LFPAK33 (SOT1210)	

6. Ordering information

Table 3. Ordering information

Type number Package						
	Name	Description	Version			
PSMN4R3-40MSH	LFPAK33	Plastic, single ended surface mounted package (LFPAK33); 8 leads; 0.65 mm pitch	SOT1210			

7. Marking

Table 4. Marking codes

Type number	Marking code
PSMN4R3-40MSH	4H3S40

8. Limiting values

Table 5. Limiting values

In accordance with the Absolute Maximum Rating System (IEC 60134).

Symbol	Parameter	Conditions		Min	Max	Unit
V_{DS}	drain-source voltage	25 °C ≤ T _j ≤ 175 °C		-	40	V
V_{DSM}	peak drain-source voltage	$t_p \le 20 \text{ ns}; f \le 500 \text{ kHz}; E_{DS(AL)} \le 200 \text{ nJ};$ pulsed		-	45	V
V_{DGR}	drain-gate voltage	25 °C ≤ T_j ≤ 175 °C; R_{GS} = 20 kΩ		-	40	V
V_{GS}	gate-source voltage			-20	20	V
P _{tot}	total power dissipation	T _{mb} = 25 °C; <u>Fig. 1</u>		-	90	W
I _D	drain current	V _{GS} = 10 V; T _{mb} = 25 °C; <u>Fig. 2</u>	[1]	-	95	А
		V _{GS} = 10 V; T _{mb} = 100 °C; <u>Fig. 2</u>		-	69	А
I _{DM}	peak drain current	pulsed; $t_p \le 10 \mu s$; $T_{mb} = 25 °C$; Fig. 3		-	392	А
T _{stg}	storage temperature			-55	175	°C
Tj	junction temperature			-55	175	°C
T _{sld(M)}	peak soldering temperature			-	260	°C
Source-drain	diode			'	'	'
I _S	source current	T _{mb} = 25 °C		-	95	А

Symbol	Parameter	Conditions		Min	Max	Unit
I _{SM}	peak source current	pulsed; t _p ≤ 10 µs; T _{mb} = 25 °C		-	392	Α
Avalanche r	uggedness					
E _{DS(AL)S}		I_D = 32.6 A; $V_{sup} \le 40$ V; R_{GS} = 50 Ω; V_{GS} = 10 V; $T_{j(init)}$ = 25 °C; unclamped; t_p = 117 μs	[2]	-	99	mJ
		I_D = 25 A; $V_{sup} \le 40$ V; R_{GS} = 50 Ω; V_{GS} = 10 V; $T_{j(init)}$ = 25 °C; unclamped; t_p = 204 μs	[2]	-	132	mJ
I _{AS}	non-repetitive avalanche current	$V_{sup} \le 40 \text{ V}; V_{GS} = 10 \text{ V}; T_{j(init)} = 25 \text{ °C};$ $R_{GS} = 50 \Omega$	[2]	-	70	А

- [1] 95A Continuous current has been successfully demonstrated during application tests. Practically the current will be limited by PCB, thermal design and operating temperature.
- [2] Protected by 100% test

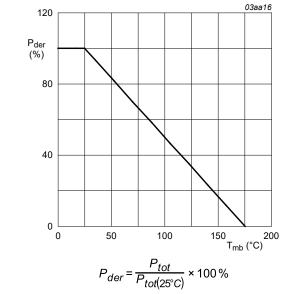
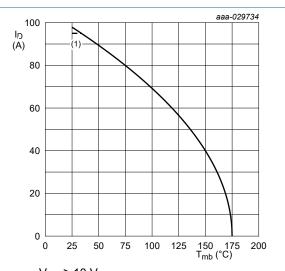
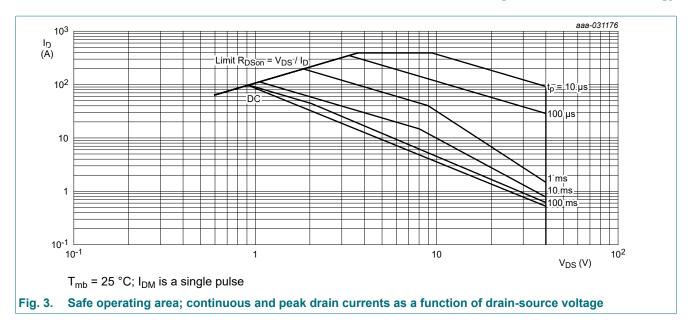


Fig. 1. Normalized total power dissipation as a function of mounting base temperature



 $V_{GS} \ge 10 \text{ V}$ (1) 95A continuous current has been successfully demonstrated during application tests. Practically the current will be limited by PCB, thermal design and operating temperature.

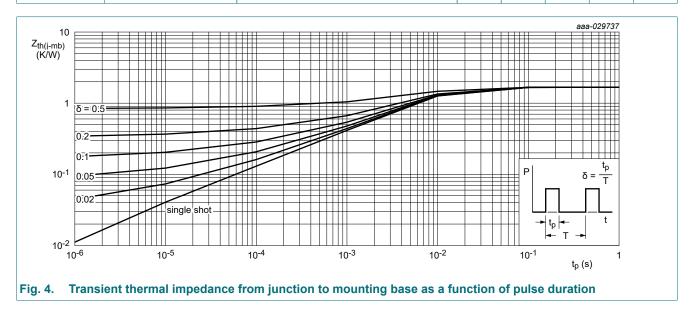
Fig. 2. Continuous drain current as a function of mounting base temperature



9. Thermal characteristics

Table 6. Thermal characteristics

Symbol	Parameter	Conditions	Min	Тур	Max	Unit
R _{th(j-mb)}	thermal resistance from junction to mounting base	Fig. 4	-	1.48	1.67	K/W
$R_{th(j-a)}$	thermal resistance from junction to ambient	Fig. 5 Fig. 6	-	50 130	-	K/W K/W



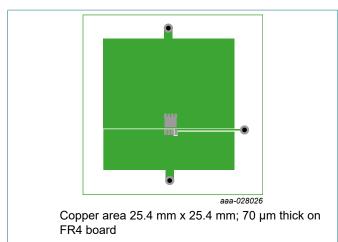
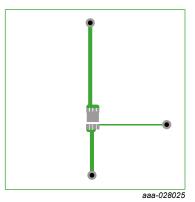


Fig. 5. PCB layout for thermal resistance from junction to ambient



70 µm thick copper on FR4 board

Fig. 6. PCB layout with minimum footprint for thermal resistance from junction to ambient

10. Characteristics

Table 7. Characteristics

Symbol	Parameter	Conditions	Min	Тур	Max	Unit
Static charac	cteristics					
V _{(BR)DSS}	drain-source	$I_D = 250 \mu A; V_{GS} = 0 V; T_j = 25 °C$	40	-	-	V
	breakdown voltage	I _D = 250 μA; V _{GS} = 0 V; T _j = -55 °C	36	-	-	V
$V_{GS(th)}$	gate-source threshold voltage	$I_D = 1 \text{ mA}; V_{DS} = V_{GS}; T_j = 25 \text{ °C}$	2.4	3	3.6	V
$\Delta V_{GS(th)}/\Delta T$	gate-source threshold voltage variation with temperature	25 °C ≤ T _j ≤ 150 °C	-	-5.9	-	mV/K
I _{DSS}	drain leakage current	$V_{DS} = 32 \text{ V}; V_{GS} = 0 \text{ V}; T_j = 25 \text{ °C}$	-	0.01	1	μΑ
		V _{DS} = 32 V; V _{GS} = 0 V; T _j = 125 °C	-	2	-	μΑ
I _{GSS}	gate leakage current	V _{GS} = 20 V; V _{DS} = 0 V; T _j = 25 °C	-	2	100	nA
		V _{GS} = -20 V; V _{DS} = 0 V; T _j = 25 °C	-	2	100	nA
R _{DSon}	drain-source on-state resistance	V_{GS} = 10 V; I_D = 25 A; T_j = 25 °C; Fig. 10	-	3.5	4.3	mΩ
		V _{GS} = 10 V; I _D = 25 A; T _j = 175 °C; Fig. 11	-	-	9.4	mΩ
R_G	gate resistance	f = 1 MHz; T _j = 25 °C	0.3	8.0	2	Ω
Dynamic cha	racteristics					
Q _{G(tot)}	total gate charge	I _D = 25 A; V _{DS} = 20 V; V _{GS} = 10 V; Fig. 12; Fig. 13	15	23	32	nC
		I _D = 0 A; V _{DS} = 0 V; V _{GS} = 10 V	-	12.3	-	nC
Q _{GS}	gate-source charge	I _D = 25 A; V _{DS} = 20 V; V _{GS} = 10 V;	4.4	7.3	11	nC
Q _{GS(th)}	pre-threshold gate- source charge	Fig. 12; Fig. 13	2.8	4.7	7	nC
Q _{GS(th-pl)}	post-threshold gate- source charge		1.5	2.6	3.8	nC
Q _{GD}	gate-drain charge	1	1.1	3.6	7.3	nC
V _{GS(pl)}	gate-source plateau voltage	I _D = 25 A; V _{DS} = 20 V; <u>Fig. 12</u> ; <u>Fig. 13</u>	-	4.5	-	V

Symbol	Parameter	Conditions		Min	Тур	Max	Unit
C _{iss}	input capacitance	V _{DS} = 25 V; V _{GS} = 0 V; f = 1 MHz;		1086	1670	2338	pF
C _{oss}	output capacitance	T _j = 25 °C; <u>Fig. 14</u>		363	559	782	pF
C _{rss}	reverse transfer capacitance			25	83	182	pF
t _{d(on)}	turn-on delay time	$V_{DS} = 20 \text{ V}; R_L = 0.8 \Omega; V_{GS} = 10 \text{ V};$		-	6.5	-	ns
t _r	rise time	$R_{G(ext)} = 5 \Omega$		-	4.5	-	ns
t _{d(off)}	turn-off delay time			-	12.4	-	ns
t _f	fall time			-	4.4	-	ns
Q _{oss}	output charge	$V_{GS} = 0 \text{ V}; V_{DS} = 20 \text{ V}; f = 1 \text{ MHz};$ $T_j = 25 \text{ °C}$		-	17.2	-	nC
Source-dra	ain diode						
V _{SD}	source-drain voltage	$I_S = 25 \text{ A}; V_{GS} = 0 \text{ V}; T_j = 25 \text{ °C}; Fig. 15$		-	0.83	1	V
t _{rr}	reverse recovery time	$I_S = 25 \text{ A}; dI_S/dt = -100 \text{ A/}\mu\text{s}; V_{GS} = 0 \text{ V};$		-	26	-	ns
Q _r	recovered charge	V _{DS} = 20 V; <u>Fig. 16</u>	[1]	-	20	-	nC
t _a	reverse recovery rise time			-	16	-	ns
t _b	reverse recovery fall time			-	10	-	ns

[1] includes capacitive recovery

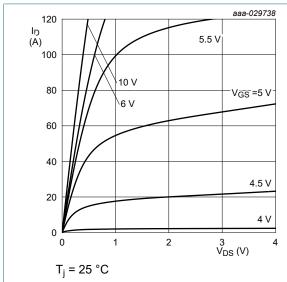


Fig. 7. Output characteristics; drain current as a function of drain-source voltage; typical values

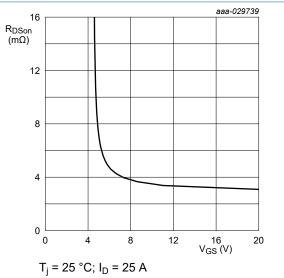


Fig. 8. Drain-source on-state resistance as a function of gate-source voltage; typical values

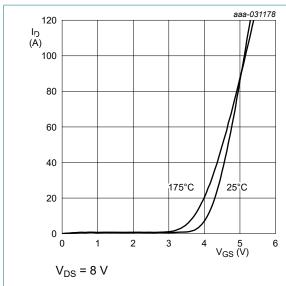


Fig. 9. Transfer characteristics; drain current as a function of gate-source voltage; typical values

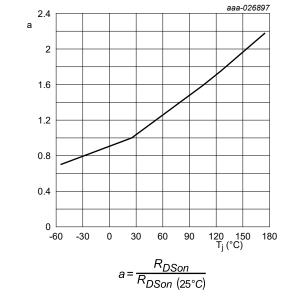


Fig. 11. Normalized drain-source on-state resistance factor as a function of junction temperature

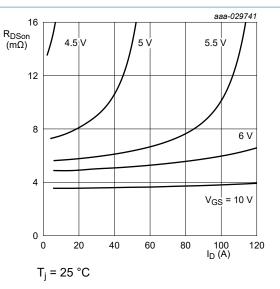


Fig. 10. Drain-source on-state resistance as a function of drain current; typical values

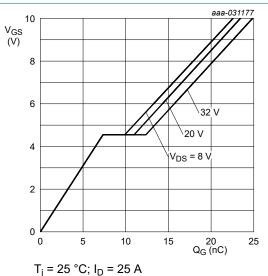


Fig. 12. Gate-source voltage as a function of gate charge; typical values

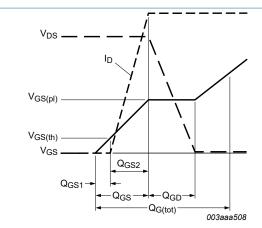
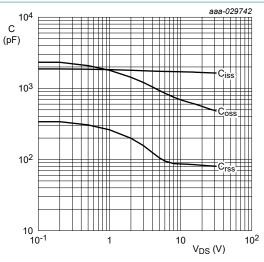


Fig. 13. Gate charge waveform definitions



 $V_{GS} = 0 V$; f = 1 MHz

Fig. 14. Input, output and reverse transfer capacitances as a function of drain-source voltage; typical values

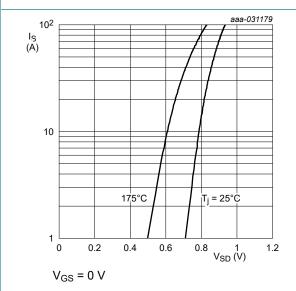


Fig. 15. Source-drain (diode forward) current as a function of source-drain (diode forward) voltage; typical values

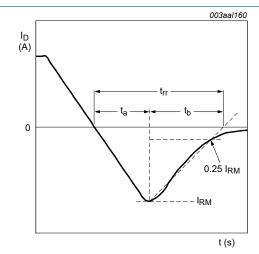


Fig. 16. Reverse recovery timing definition

11. Package outline

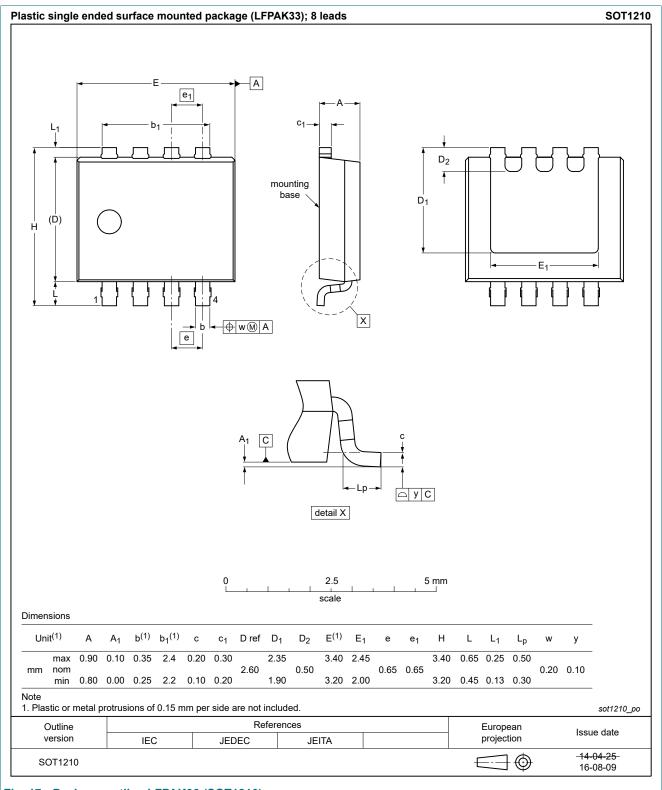
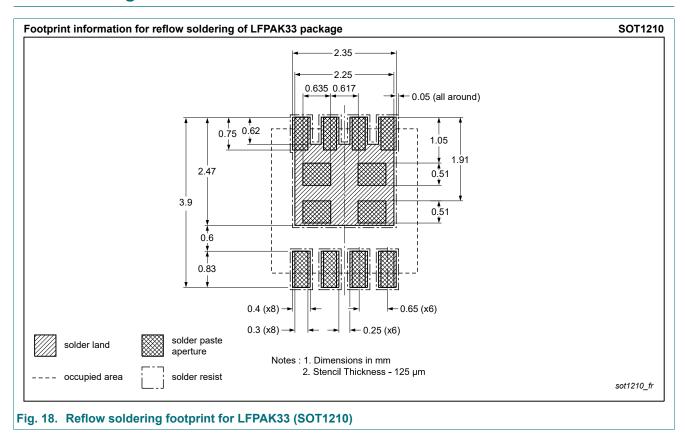


Fig. 17. Package outline LFPAK33 (SOT1210)

12. Soldering



13. Legal information

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Document status [1][2]	Product status [3]	Definition
Objective [short] data sheet	Development	This document contains data from the objective specification for product development.
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